

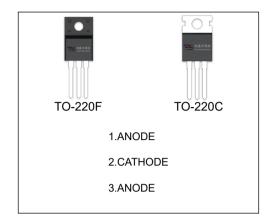
MUR1660CT , MURF1660CT SUPER FAST

MAIN CHARACTERISTICS

Io	16A
V_{RRM}	600 V
Tj	150 ℃
V _{F(typ)}	1.17V (@Tj=125℃)

FEATURES

- Ultrafast 35ns Recovery Times
- High Voltage Capability to 600V
- Low Reverse Leakage Current



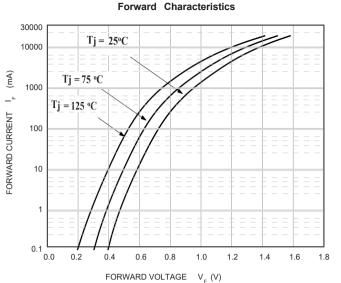
MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

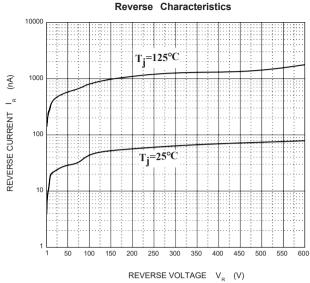
Symbol	Davanatas	MU	l lm:4	
Symbol	Parameter	1660CT	F1660CT	Unit
V_{RRM}	Peak repetitive reverse voltage	600		V
V _{RWM}	Working peak reverse voltage			
V _R	DC blocking voltage			
V _{R(RMS)}	RMS reverse voltage	420		V
	Average rectified output current@ Per leg	8		А
I _o	Average rectified output current@ Total device	16		А
I _{FSM}	Non-Repetitive peak forward surge current 8.3ms half sine wave		10	А
P _D	Power dissipation 2.0		W	
R _{OJA}	Thermal resistance from junction to ambient	62.5		°C/W
T _j	Operating Junction Temperature Range	-55 ~ +150		°C
T _{stg}	Storage Temperature Range -55 ~ +150		+150	℃

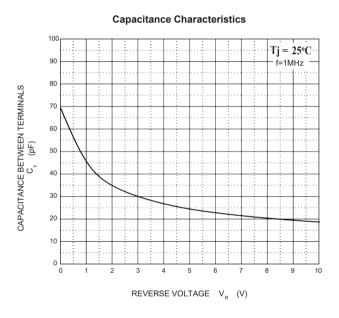
ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions		Min	Тур	Max	Unit
Reverse voltage	V _(BR)	I _R =100uA		600			V
Reverse current	I _R	V _R =600V	Tj =25℃		0.1	1	uA
			Tj =125℃		2.0		uA
Forward voltage	V _F	I==8.0A	Tj =25℃		1.35	1.6	V
			Tj =125℃		1.17		V
Typical total capacitance	C _{tot}	V _R =4.0V,f=1MHz			28		pF
Reverse recovery time	t _{rr}	I _F = 0.5A, I _R =1A,I _{rr} =0.25A				35	ns









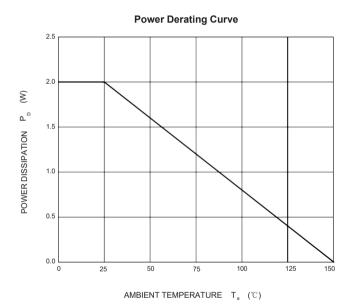


Diagram of circuit and Testing wave form of reverse recovery time

